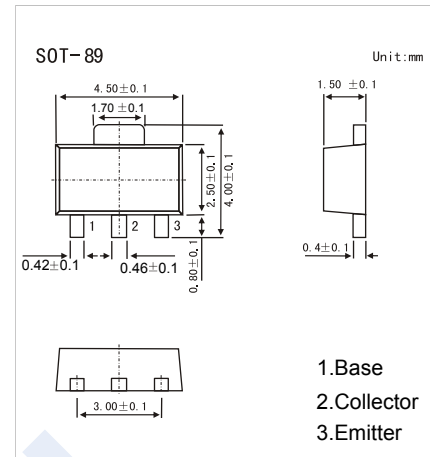


PNP Transistors

2SA1419-HF

■ Features

- Adoption of FBET, MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Complementary to 2SC3649-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-180	V
Collector - Emitter Voltage	V_{CE0}	-160	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-1.5	A
Collector Current - Pulsed	I_{CP}	-2.5	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-180			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}$, $R_{BE} = \infty$	-160			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -120 \text{ V}$, $I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 \text{ V}$, $I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -25 \text{ mA}$		-0.2	-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -25 \text{ mA}$		-0.85	-1.2	
DC current gain	h_{FE}	$V_{CE} = -5 \text{ V}$, $I_C = -100 \text{ mA}$	100		400	
		$V_{CE} = -5 \text{ V}$, $I_C = -10 \text{ mA}$	80			
Turn-on time	t_{on}	See Test Circuit.		40		ns
Storage time	t_s			700		
Fall time	t_f			40		
Output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		22		pF
Transition frequency	f_T	$V_{CE} = -10 \text{ V}$, $I_E = -50 \text{ mA}$		120		MHz

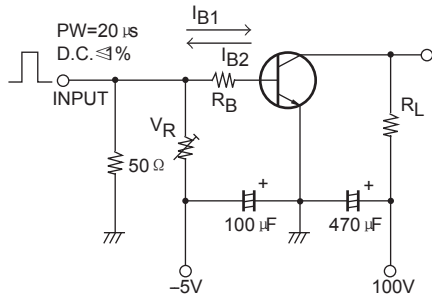
■ Classification of h_{FE}

Type	2SA1419-R-HF	2SA1419-S-HF	2SA1419-T-HF
Range	100-200	140-280	200-400
Marking	AER* _F	AES* _F	AET* _F

PNP Transistors

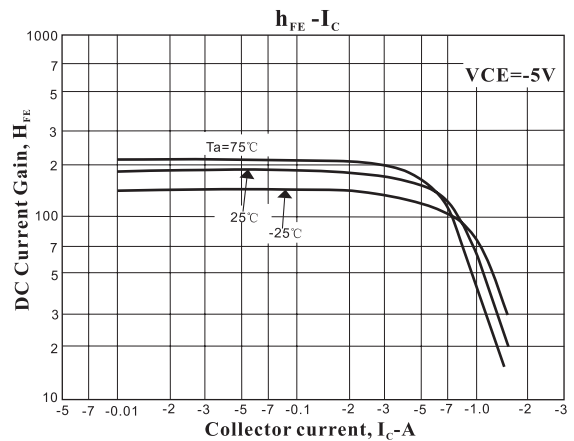
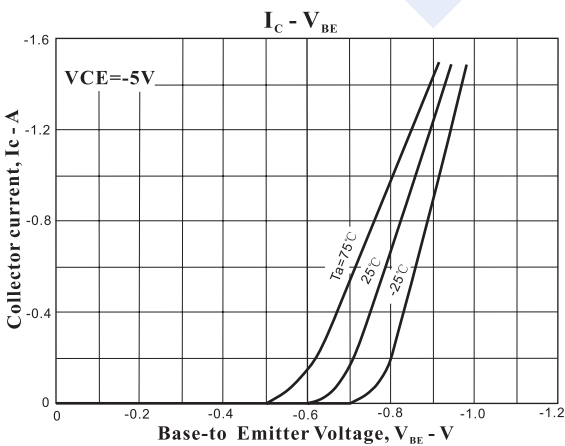
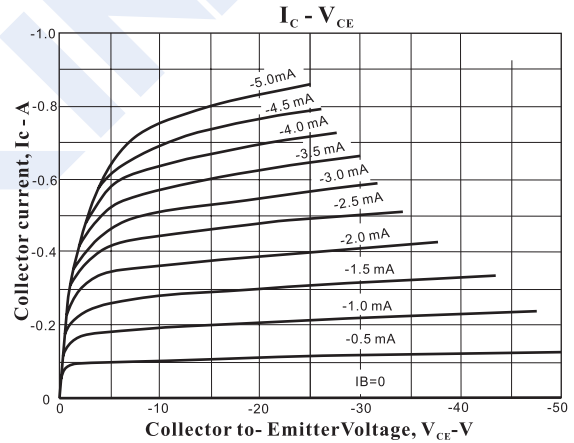
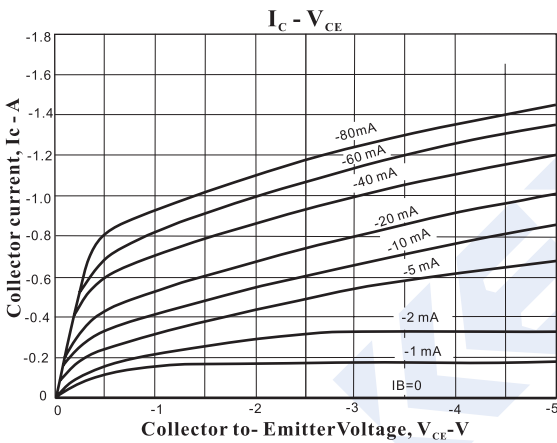
2SA1419-HF

■ Test Circuit



$I_C = 10I_{B1} = -10I_{B2} = 0.7A$
 (For PNP, the polarity is reversed)

■ Typical Characteristics



PNP Transistors

2SA1419-HF

Typical Characteristics

